

(12) United States Patent

Okandan et al.

(54) STRUCTURED WAFER FOR DEVICE **PROCESSING**

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See application file for complete search history.

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ABSTRACT (57)

A structured wafer that includes through passages is used for device processing. Each of the through passages extends from or along one surface of the structured wafer and forms a pattern on a top surface area of the structured wafer. The top surface of the structured wafer is bonded to a device layer via a release layer. Devices are processed on the device layer, and are released from the structured wafer using etchant. The through passages within the structured wafer allow the etchant to access the release layer to thereby remove the release layer.

20 Claims, 7 Drawing Sheets

